DYNAMIC PROCESS GROUP, INC.

SOI Wafers

Item No.	Wafer Type & Size	Device Layer Specifications	BOX Thickness	Handle Wafer Specifications	Additional Details	Qty	MOQ		
Item No.1	**4 inch SOI Wafer**	N/Ph, Res: 3.87–4.53 Ω·cm, Thick: 12.0–12.4 µm, Orientation: 100±0.5	0.31 µm ±5%	N/Ph, Res: 3.87–4.53 Ω·cm, Orientation: 100±0.5, Total Thick: 362.5–362.7 µm	DSP	2	2		
Item No.2	**4 inch SOI Wafer**	P/B, Res: 3.96–4.35 Ω·cm, Thick: 4.6–5.5 µm, Orientation: 100±1.5	0.98–0.99 µm	P/B, Res: 3.96–4.35 Ω·cm, Orientation: 100±1.0, Total Thick: 307.8–309.1 µm	DSP	7	2		
Item No.3	**4 inch SOI Wafer, 1 Flat**	FZ, Res: >10,000 Ω·cm, Thick: 250±1.0 µm, Orientation: <100>, Finish: Polished	2.0 µm ±5%	FZ, Res: >10,000 Ω·cm, Thick: 750±5 µm, Orientation: <100>, Finish: Polished with 2 µm oxide	—	2	2		
Item No.4	**4 inch SOI Wafer, 2 Flats**	P/B, Res: 0.01–0.02 Ω·cm, Thick: 150±10.0 µm, Orientation: <100>, Finish: Polished	3.0 µm ±5%	P/B, Res: 1–20 Ω·cm, Thick: 525±25 µm, Orientation: <100>, Finish: Etched with 3 µm oxide	—	8	2		
Item No.5	**8 inch SOI Wafer**	P/B, Res: 1–100 Ω·cm, Thick: 70 nm, Orientation: <100>	2.0 µm ±5%	P/B, Res: 1–100 Ω·cm, Thick: 725 µm, Orientation: <100>	Test / dummy grade. CoC covers the listed specs only.	18	2		
Item No.6	**4 inch Layer-Transfer SOI Wafer**	Thick: 200±10 nm, Orientation: <100>	0.12±0.01 µm	Thick: 200±10 µm, Orientation: <100>, Finish: Backside Polished	—	2	2		
Item No.7	**4 inch Layer-Transfer SOI Wafer, 2 Flats, Nano-ground Back Side**	P/B, Res: >1–10 Ω·cm, Thick: 220±5 nm, Orientation: <100>	3.0 µm ±5%	P/B, Res: >750 Ω·cm, Thick: 525±25 µm, Orientation: <100>	—	25	2		